# A Cross-Coupled Type AC-DC Converter for Remote Power Feeding to a RFID Tag 

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Abstract: In this paper, a cross-coupled type AC-DC converter for RFID tags is proposed. The converter consists of 2 charge-pump type AC-DC converters with opposite polarities. In conventional converters, the threshold voltage of a diode switch causes the decrease in power efficiency. By using cross-coupled connection of CMOS switches, the proposed converter can alleviate the influence of the threshold voltage. Hence, it can achieve an AC-DC conversion with high efficiency. Furthermore, the circuit size of the proposed converter is almost the same as that of the conventional circuit. Through SPICE simulations, the following characteristics are obtained: 1. the power efficiency is more than $88 \%$ and 2 . the electric power is about 5 mW when an output load is $500 \Omega$. Concerning the power efficiency and the ripple voltage, theoretical design formulas are derived. Furthermore, the validity of the circuit design is confirmed by experiments.

Key-Words: AC-DC Converters, Switched-Capacitor Circuits, Charge-Pump Circuits, Power Converters, RFID Tags, RF Electromagnetic Induction

## 1 Introduction

RFID (Radio Frequency IDentification) systems manage information with tags which embedded noncontact radio chips. Recently, RFID tags [1-13] attract much attention as a basic technology of IT (Information Technology). Concretely, they are used in the fields of traffic control [6], security systems [9], etc. [1-13]. In our laboratory, a RFID tag is being developed to measure biomedical signals of transgenic mice [10-13]. In order to supply electric power to the RFID tag implanted into the transgenic mice, remote power feeding is used in the system. The RFID tag is
classified into an active-type and a passive-type. However, in the active-type, an external battery is required in order to operate a tag. Therefore, we employ the passive-type RFID tags, because the size of activetype RFID tags is large and heavy.

In the passive-type RFID tags, the remote power feeding is achieved by using RF electro-magnetic induction. Therefore, to convert AC voltages provided by power receiving coils, AC-DC converters [10-17] are necessary in the tags. For example, step-up type AC-DC converters are employed in the RFID tags proposed in [10-13]. These converters consist of diode switches and capacitors. In the design of the AC-DC

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Fig. 1 Conventional AC-DC converter.


Fig. 2 Power receiving coils.
converters for RFID tags, to suppress adverse effects caused by heat, the converters which can realize high power efficiency as well as small chip area are desirable. However, in the conventional converters [11-13], threshold voltage drop caused by diode-switches decreases the power efficiency.

In this paper, a cross-coupled type AC-DC converter for RFID tags is proposed. The converter consists of 2 charge-pump type [18-22] AC-DC converters with opposite polarities. Instead of the diodeswitches, the proposed converter employs CMOS switches which are controlled by using cross-coupled connection. Hence, it can achieve an AC-DC conversion with high efficiency, because the cross-coupled connection of CMOS switches alleviates the threshold voltage drop. Furthermore, the circuit size of the proposed converter is almost the same as that of the conventional circuit.

The circuit design and characteristics of the converter are analyzed through theoretical analyses and simulations, and the experimental circuit is fabricated with commercially available transistors.

## 2 Circuit Structure

### 2.1 Conventional Converter

Figure 1 shows a charge-pump type AC-DC converter proposed in [11-13]. In RFID tag systems, remote power feeding systems using RF electromagnetic induction are used. In Fig.1, a pair of power receiv-


Fig. 3 Proposed AC-DC converter.
ing coils is modeled by a pair of AC voltage sources with opposite polarities. Figure 2 shows a model the power receiving coils. The conventional converter of Fig. 1 consists of 2 charge-pump type AC-DC converters with opposite polarities. The converter shown in Fig. 1 can supply a stepped-up DC voltage. After the AC-DC conversion, the output DC voltage is regulated by a series regulator.

For easy understanding of the circuit operation, let us consider the converter block-1. When the input voltage $V_{i n+}$ is in State $-T 2^{1}$ (see in Fig.1), the diode $D_{2+}$ is turned on. Then the voltage of $C_{1+}$ becomes about $V_{m}-V_{t h}$, where $V_{m}$ and $V_{t h}$ denote the amplitude voltage of AC input and the threshold voltage of the diode, respectively. Next, when the input voltage $V_{\text {in+ }}$ is in State - T1 (see in Fig.1), the diode $D_{1+}$ is turned on. Then the output voltage of the converter becomes about $2\left(V_{m}-V_{t h}\right)$. Hence, the threshold voltage drop caused by diodes affects the power efficiency of the conventional converter. In this paper, we solve this problem by using cross-coupled connection of CMOS switches.

### 2.2 Proposed Converter

Figure 3 shows the proposed AC-DC converter. The converter is designed to receive power by electromagnetic induction in the dozens MHz range. In Fig.3, MOS transistors are used instead of the diodes in Fig.1. As Figs. 1 and 3 show, the circuit size of the proposed converter is almost the same ${ }^{2}$ as that of the

[^0]conventional circuit. The operation of the converter block-1 is as follows.

When the input voltage $V_{i n+}$ is in State $-T 2$ (see in Fig.3), the transistor $M_{2+}$ is turned on, because the gate terminal of $M_{2+}$ is connected to another input terminal with opposite polarity, $V_{i n-}$. Therefore, the voltage of $C_{1+}$ becomes $V_{m}$. At the same time, the transistor $M_{1+}$ is turned off since the gate terminal of $M_{1+}$ is connected to the right terminal of $C_{1-}{ }^{3}$.

Next, when the input voltage $V_{i n+}$ is in State $T 1$ (see in Fig.3), the transistor $M_{2+}$ is turned off. At the same time, the transistor $M_{1+}$ is turned on, because the gate terminal of $M_{1+}$ is grounded via $M_{2-}$. Hence, the output voltage of the converter becomes about $2 V_{m}$. By iterating these operations, the proposed converter supplies a stepped-up DC voltage.

## 3 Theoretical Analysis

### 3.1 Equivalent Circuit and Power Efficiency

The equivalent circuit and the power efficiency of the proposed converter are analyzed theoretically. To simplify the theoretical analyses, we assume that the time constant $R_{L} C_{2+}$ and $R_{L} C_{2-}$ are quite larger than $T$ and parasitic elements are not effective.

Firstly, the equivalent circuit of the converter block-1 is analyzed. The instantaneous equivalent circuits of the converter block can be expressed by the circuits shown in Fig.4. In Fig.4, $R_{\delta k}(k=1,2)$ denotes a resistor to model a dielectric loss.

In the steady state, the differential values of the electric charges in $C_{1+}$ and $C_{2+}$ satisfy

$$
\begin{equation*}
\Delta q_{T 1}^{k}+\Delta q_{T 2}^{k}=0 \quad(k=1,2) \tag{1}
\end{equation*}
$$

where $\Delta q_{T 1}^{k}$ and $\Delta q_{T 2}^{k}$ denote the electric charges when $T 1$ and $T 2$, respectively. The intervals of State - T1 and State $-T 2, T 1$ and $T 2$, satisfy the following conditions:

$$
\begin{array}{ll} 
& T=T 1+T 2, \\
& T 1=D T, \\
\text { and } \quad & T 2=(1-D) T, \tag{2}
\end{array}
$$

where $T$ is a period of the input voltage and $D$ denotes a duty factor (see in Fig.3).

In the case of State $-T 1$, the currents which flow $C_{k+}$ and $R_{\delta k}$ are given by

$$
\Delta q_{T 1}^{k} / T_{1} \quad \text { and } \quad\left(q_{T 1}^{k} / T_{1}\right) \tan \delta_{k},
$$

capacitors.
${ }^{3}$ In this timing, the node voltage of the right terminal of $C_{1-}$ is about $2 V_{m}$.


Fig. 4 Instantaneous equivalent circuits of converter block-1. (a) State $-T 1$. (b) State $-T 2$.
respectively, where $\delta_{k}$ denotes a dielectric loss angle. Thus the differential values of the electric charges in the input and the output terminals, $\Delta q_{\Gamma 1, V_{i n}}$ and $\Delta q_{T 1, V_{\text {out }}}$, are given by

$$
\text { and } \quad \begin{align*}
\Delta q_{T 1, V_{\text {in }}} & =\Delta q_{T 1}^{1}\left(1+\tan \delta_{1}\right) \\
\Delta q_{T 1, V_{\text {out }}} & =\Delta q_{T 1}^{2}\left(1+\tan \delta_{2}\right) \\
& -\Delta q_{T 1}^{1}\left(1+\tan \delta_{1}\right), \tag{3}
\end{align*}
$$

respectively. On the other hand, in the case of State $T 2$, the currents which flow $C_{k+}$ and $R_{\delta k}$ are given by

$$
\Delta q_{T 2}^{k} / T_{2} \quad \text { and } \quad\left(q_{T 2}^{k} / T_{2}\right) \tan \delta_{k}
$$

respectively. Thus $\Delta q_{T 2, V_{\text {in }}}$ and $\Delta q_{T 2, V_{\text {out }}}$, are given by

$$
\begin{array}{ll} 
& \Delta q_{T 2, V_{\text {in }}}=\Delta q_{T 2}^{1}\left(1+\tan \delta_{1}\right) \\
\text { and } \quad & \Delta q_{T 2, V_{\text {out }}}=\Delta q_{T 2}^{2}\left(1+\tan \delta_{2}\right), \tag{4}
\end{array}
$$

respectively. Here, the electric charges in the input and the output, $\Delta q_{V_{i n}}$ and $\Delta q_{V_{o u t}}$, are given by

$$
\text { and } \begin{align*}
& \Delta q_{V_{\text {in }}}=\Delta q_{T 1, V_{\text {in }}}+\left(-\Delta q_{\left.T 2, V_{\text {in }}\right)}\right) \\
& \Delta q_{V_{\text {out }}}=\Delta q_{T 1, V_{\text {out }}}+\Delta q_{T 2, V_{\text {out }}},
\end{align*}
$$

respectively. By substituting Eqs.(1), (3), and (4) into Eq.(5), the following equations are derived:
and

$$
\begin{aligned}
\Delta q_{V_{\text {in }}} & =2 \Delta q_{T 1}^{1}\left(1+\tan \delta_{1}\right) \\
\Delta q_{V_{\text {out }}} & =-\Delta q_{T 1}^{1}\left(1+\tan \delta_{1}\right), \\
\Delta q_{V_{i n}} & =-2 \Delta q_{V_{\text {out }}}, \\
\overline{I_{\text {in }}} & =-2 \overline{I_{\text {out }}},
\end{aligned}
$$

where $\overline{I_{\text {in }}}$ and $\overline{I_{\text {out }}}$ denote an averaged input current and an averaged output current, respectively.

In Fig.4, the energy consumed by resistors in 1period, $W_{S C}$, can be expressed by

$$
\begin{equation*}
W_{S C}=W_{T 1}+W_{T 2}, \tag{7}
\end{equation*}
$$

where

$$
\begin{aligned}
W_{T 1} & =\frac{\left(R_{i n}+R_{o n 1}\right) \cdot\left\{\Delta q_{T 1}^{1}\left(1+\tan \delta_{1}\right)\right\}^{2}}{T 1} \\
& +\frac{R_{\delta 1} \cdot\left(\Delta q_{T 1}^{1} \tan \delta_{1}\right)^{2}}{T 1}+\frac{R_{\delta 2} \cdot\left(\Delta q_{T 1}^{2} \tan \delta_{2}\right)^{2}}{T 1}
\end{aligned}
$$

and

$$
\begin{aligned}
W_{T 2} & =\frac{\left(R_{i n}+R_{o n 2}\right) \cdot\left\{\Delta q_{T 2}^{1}\left(1+\tan \delta_{1}\right)\right\}^{2}}{T 2} \\
& +\frac{R_{\delta 2} \cdot\left(\Delta q_{T 2}^{2} \tan \delta_{2}\right)^{2}}{T 2} .
\end{aligned}
$$

In Fig. 4 (a) and (b), the following equations can be obtained by Kirchhoff's law:

$$
\begin{aligned}
\overline{V_{i n}} \cdot T 1 & =R_{\delta_{2}} \Delta q_{T 1}^{2} \tan \delta_{2}-R_{\delta_{1}} \Delta q_{T 1}^{1} \tan \delta_{1} \\
& -\left(R_{\text {in }}+R_{o n 1}\right)\left(1+\tan \delta_{1}\right) \Delta q_{T 1}^{1}
\end{aligned}
$$

and

$$
\begin{align*}
-\overline{V_{\text {in }}} \cdot T 2 & =R_{\delta_{1}} \Delta q_{T 2}^{1} \tan \delta_{1} \\
& +\left(R_{\text {in }}+R_{\text {on } 2}\right)\left(1+\tan \delta_{1}\right) \Delta q_{T 2}^{1} . \tag{8}
\end{align*}
$$

By substituting Eq.(2) into (8), the following equation can be derived:

$$
\begin{align*}
& \Delta q_{T 1}^{2} \tan \delta_{2}= \\
& \quad \Delta q_{T 1}^{1} \cdot \frac{D}{R_{\delta_{2}}}\left\{\left(R_{\delta_{1}} \tan \delta_{1}\right)\left(\frac{1}{D}+\frac{1}{1-D}\right)\right. \\
& \left.\quad+\left(1+\tan \delta_{1}\right)\left(\frac{R_{i n}+R_{o n 1}}{D}+\frac{R_{i n}+R_{o n 2}}{1-D}\right)\right\} . \tag{9}
\end{align*}
$$

When the proposed circuit satisfies the following conditions:

$$
\begin{aligned}
& D=1 / 2, \\
& R_{o n} \equiv R_{o n 1}=R_{o n 2}, \\
& R_{\delta} \equiv R_{\delta 1}=R_{\delta 2},
\end{aligned}
$$

$$
\begin{equation*}
\text { and } \tan \delta \equiv \tan \delta_{1}=\tan \delta_{2}, \tag{10}
\end{equation*}
$$

Eq.(9) can be rewritten as

$$
\begin{align*}
& \Delta q_{T 1}^{2} \tan \delta=-\Delta q_{V_{\text {out }}} \cdot \frac{2}{R_{\delta}(1+\tan \delta)} \\
& \quad \cdot\left\{R_{\text {in }}+R_{\text {on }}+\left(R_{\text {in }}+R_{\text {on }}+R_{\delta}\right) \tan \delta\right\} . \tag{11}
\end{align*}
$$



Fig. 5 Equivalent circuit of step-up SC converter.

Under the conditions of Eq.(10), we derive the following equations by substituting Eqs.(1), (6) and (11) into Eq.(7):

$$
\begin{aligned}
& W_{T 1}=2\left(R_{\text {in }}+R_{\text {on }}\right) \frac{\left(\Delta q_{V_{\text {out }}}\right)^{2}}{T} \\
& +2 R_{\delta}\left(\frac{\tan \delta}{1+\tan \delta}\right)^{2} \frac{\left(\Delta q_{V_{\text {out }}}\right)^{2}}{T} \\
& +2 R_{\delta}\left[\frac{2\left\{R_{\text {in }}+R_{\text {on }}+\left(R_{\text {in }}+R_{\text {on }}+R_{\delta}\right) \tan \delta\right\}}{R_{\delta}(1+\tan \delta)}\right]^{2} \\
& . \frac{\left(\Delta q_{V_{\text {out }}}\right)^{2}}{T}
\end{aligned}
$$

and

$$
\begin{align*}
& W_{T 2}=2\left(R_{\text {in }}+R_{\text {on }}\right) \frac{\left(\Delta q_{V_{\text {out }}}\right)^{2}}{T} \\
& +2 R_{\delta}\left[\frac{2\left\{R_{\text {in }}+R_{\text {on }}+\left(R_{\text {in }}+R_{\text {on }}+R_{\delta}\right) \tan \delta\right\}}{R_{\delta}(1+\tan \delta)}\right]^{2} \\
& \qquad \frac{\left(\Delta q_{V_{\text {out }}}\right)^{2}}{T} . \tag{12}
\end{align*}
$$

Here, it is known that a general equivalent circuit of SC power converters can be expressed by the circuit of Fig. 5 [23-25], where $\overline{V_{i n}}$ denotes an averaged voltage of $\left|V_{\text {in }}\right|\left(\right.$ or $\left.\left|V_{\text {in- }}\right|\right)$ and $\overline{V_{\text {out }}}$ is an averaged voltage of $V_{\text {out }}$. The consumed energy $W_{S C}$ in Fig. 5 is defined by

$$
\begin{align*}
W_{S C} & =W_{T 1}+W_{T 2} \\
& \equiv\left(\frac{\Delta q_{V_{\text {out }}}}{T}\right)^{2} \cdot R_{S C} \cdot T . \tag{13}
\end{align*}
$$

From Eqs.(12) and (13), the resistance $R_{S C}$ in Fig. 5 is expressed by

$$
\begin{align*}
& R_{S C}=4\left(R_{\text {in }}+R_{\text {on }}\right)+2 R_{\delta}\left(\frac{\tan \delta}{1+\tan \delta}\right)^{2} \\
& +16 R_{\delta}\left\{\frac{R_{\text {in }}+R_{o n}+\left(R_{\text {in }}+R_{\text {on }}+R_{\delta}\right) \tan \delta}{R_{\delta}(1+\tan \delta)}\right\}^{2} . \tag{1}
\end{align*}
$$

Here, the dielectric loss tangent $\tan \delta$ is given by

$$
\begin{equation*}
\tan \delta=\frac{1}{2 \pi f C R_{\delta}} \tag{15}
\end{equation*}
$$

Hence, Eq.(14) can be rewritten as

$$
R_{S C}=4\left(R_{i n}+R_{o n}\right)+\frac{2 R_{\delta}}{\left(1+2 \pi f C R_{\delta}\right)^{2}}
$$



Fig. 6 Equivalent circuit of proposed converter.

$$
\begin{equation*}
+\frac{16}{R_{\delta}}\left\{\frac{2 \pi f C R_{\delta}\left(R_{i n}+R_{o n}\right)+\left(R_{i n}+R_{o n}+R_{\delta}\right)}{1+2 \pi f C R_{\delta}}\right\}^{2} . \tag{16}
\end{equation*}
$$

The equivalent circuit of Fig. 5 can be expressed by the determinant using Kettenmatrix. Therefore, by using Eqs.(6) and (16), the equivalent circuit of the converter block can be given by the following determinant:

$$
\left[\begin{array}{c}
\overline{V_{\text {in }}}  \tag{17}\\
\overline{I_{\text {in }}}
\end{array}\right]=\left[\begin{array}{cc}
1 / 2 & 0 \\
0 & 2
\end{array}\right]\left[\begin{array}{cc}
1 & R_{S C} \\
0 & 1
\end{array}\right]\left[\begin{array}{c}
\overline{V_{\text {out }}} \\
\overline{I_{\text {out }}}
\end{array}\right] .
$$

Hence, from Eq.(17), the equivalent circuit of the proposed converter can be expressed by the circuit shown in Fig.6. From Fig.6, the power efficiency $\eta$ can be given by

$$
\begin{align*}
\eta & =\frac{\left(\overline{I_{\text {out }}}\right)^{2} R_{L}}{\left(\overline{\overline{\text { out }}^{L}} / 2\right)^{2} R_{S C}+\left(\overline{\text { out }_{\text {ou }}} / 2\right)^{2} R_{S C}+(\overline{\overline{o u t}})^{2} R_{L}} \\
& =\frac{R_{L}}{R_{S C} / 2+R_{L}} . \tag{18}
\end{align*}
$$

Especially, when the input voltage is a rectangular wave (i.e. $R_{\delta}=\infty$ ), the efficiency $\eta$ can be expressed by

$$
\begin{equation*}
\eta=\frac{R_{L}}{2\left(R_{i n}+R_{o n}\right)+R_{L}}, \tag{19}
\end{equation*}
$$

because the resistance $R_{S C}$ can be expressed from Eq.(14) as

$$
\begin{equation*}
R_{S C}=4\left(R_{i n}+R_{o n}\right) \tag{20}
\end{equation*}
$$

The comparison of the power efficiency between the proposed converter and the conventional converter will be discussed in Appendix.

### 3.2 Ripple Voltage

In this subsection, the ripple voltage of the converter block-1 is analyzed by assuming that $R_{\delta 1}=R_{\delta 2}=$ $\infty$. In State $-T 2$, we define that the electric charge $2 \Delta Q$ consumed by the output load $R_{L}$ is charged in $C_{1+}$. Then, $2 \Delta Q$ can be expressed by

$$
\begin{equation*}
2 \Delta Q=\overline{I_{L}}(1-D) T \tag{21}
\end{equation*}
$$



Fig. 7 Instantaneous equivalent circuit in State $-T 1$.
where $\overline{I_{L}}$ denotes an averaged charge current of $C_{1+}$. In the steady state, the instantaneous equivalent circuit of Fig. 4 (a) can be rewritten as the circuit shown in Fig.7, where $V_{m}$ and $\overline{V_{o u t}}$ denote a positive maximum value of the input voltage and an averaged output voltage, respectively. From Fig.7, by assuming the steady state, the following equation can be obtained by Kirchhoff's voltage law:

$$
\begin{aligned}
& 2 V_{m}-\left(R_{\text {in }}+R_{\text {on } 2}\right) \overline{I_{L}} \\
& \quad=\overline{V_{\text {out }}}+\left(R_{\text {in }}+R_{\text {on } 1}\right)\left(\overline{I_{L}}+2 \Delta Q / D T\right) \\
& \quad+\Delta Q / C_{2+}+\left(\Delta Q+\overline{I_{L}} D T / 2\right) / C_{1+}
\end{aligned}
$$

and

$$
\begin{equation*}
\overline{V_{\text {out }}}=\overline{I_{L}} R_{L} . \tag{22}
\end{equation*}
$$

From Eqs.(21) and (22), the averaged output voltage $\overline{V_{\text {out }}}$ can be given by

$$
\begin{equation*}
\overline{V_{o u t}}=\frac{2 D R_{L} V_{m}}{D m} \tag{23}
\end{equation*}
$$

where

$$
\begin{aligned}
D m= & \left\{(D+1) R_{i n}+D R_{L}+R_{o n 1}+D R_{o n 2}\right\} \\
& +\frac{D T}{2}\left(\frac{1-D}{C_{2+}}+\frac{1}{C_{1+}}\right) .
\end{aligned}
$$

When the converter block satisfies the conditions of Eq.(10), Eq.(23) can be rewritten as

$$
\begin{equation*}
\overline{V_{\text {out }}}=\frac{8 C R_{L} V_{m}}{4 C\left\{3\left(R_{\text {in }}+R_{\text {on }}\right)+R_{L}\right\}+3 T} \tag{24}
\end{equation*}
$$

Here, from Fig. 7 and Eqs.(21) and (22), the ripple voltage of the converter block-1, $V_{\text {rip-1 }}$, can be expressed by

$$
\begin{align*}
V_{\text {rip }-1} & =\frac{\Delta Q}{C} \\
& =\frac{\overline{I_{L}}(1-D) T}{2 C}=\frac{T}{4 C R_{L}} \cdot \overline{V_{\text {out }}} . \tag{25}
\end{align*}
$$

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Table 1 Size of transistors used in simulations.

| Transistor | Size |
| :--- | :---: |
| $M_{1+}, M_{1-}$ | $\mathrm{L}=1.48 \mu \mathrm{~m}, \mathrm{~W}=17.76 \mu \mathrm{~m}$ |
| $M_{2+}, M_{2-}$ | $\mathrm{L}=1.48 \mu \mathrm{~m}, \mathrm{~W}=8.88 \mu \mathrm{~m}$ |



Fig. 8 Simulated power efficiency.

## 4 Simulation

To confirm the effectiveness of the proposed converter, SPICE simulations were performed concerning the circuit shown in Figs. 1 and 3. To be compatible with process limitations on the maximum allowable voltage on a chip, we adopted a 2 -metal 2 -poly 1.2 $\mu \mathrm{m}$ CMOS process. The size of transistors used in SPICE simulations is shown in Table 1.

Figure 8 shows the simulated power efficiency. The SPICE simulations of Fig. 8 were performed under the conditions that $V_{i n+}=-V_{i n-}=1 \mathrm{~V} @ 40 \mathrm{MHz}$, $C_{1+}=C_{1-}=C_{2+}=C_{2-}=500 \mathrm{pF}$, and $R_{i n}=0.1$ $\Omega$. As Fig. 8 shows, the proposed converter can improve the power efficiency ${ }^{4}$. When the output load is $500 \Omega$, the power efficiency of the proposed converter is more than $88 \%$ and the electric power is about 5 mW .

Figure 9 shows the simulated ripple voltage. As Fig. 9 shows, the ripple voltage of the proposed converter and the conventional converter is almost the same. When the output load is $500 \Omega$, the ripple voltage is about 0.03 V .

## 5 Experiment

To confirm the validity of circuit design, the experiment was performed regarding to the proposed circuit shown in Fig.3. The experimental circuit was built

[^1]

Fig. 9 Simulated ripple voltage.


Fig. 10 Experimental result.
with a FCZ1.9-type coil and commercially available transistors 2SK214 and 2SJ77 on a bread board.

Figure 10 shows the result of AC-DC conversion obtained by the experimental circuit. In Fig.10, the experiment was performed under the conditions that the AC input voltage $V_{p-p}=1 \mathrm{~V}$ at 2 MHz and the capacitors $C_{1+}=C_{1-}=C_{2+}=C_{2-}=10 \mathrm{nF}$. As Fig. 10 shows, the proposed converter can achieve ACDC conversion ${ }^{5}$.

## 6 Conclusion

In this paper, a cross-coupled type AC-DC converter for RFID tags has been proposed. By using crosscoupled connection of CMOS switches, the proposed converter can achieve an AC-DC conversion at high efficiency.

The SPICE simulations showed that 1 . the power efficiency of the proposed converter is more than 88

[^2]$\%, 2$. the electric power is about 5 mW when the output load is $500 \Omega$, and 3 . the ripple voltage and the circuit size of the proposed converter are almost the same as that of the conventional converter. Furthermore, the formulas obtained by the theoretical analyses will be useful for designing the proposed converter.

Due to the limitation of the speed of MOSFET's, the proposed converter will be applied for low and high frequency ( $134 \mathrm{KHz} \& 13.56 \mathrm{MHz}$ ) tags such as package delivery, access control, and payment devices. The IC implementation and experiments are left to the future study.

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## References:

[1] S.Shepard, RFID: Radio Frequency Identification, New York: McGraw-Hill, 2005.
[2] K.Rongsawat and A.Thanachayanont, Ultra low power analog front-end for UHF RFID transponder, Proc. of the International Symposium on Communications and Information Technologies 2006, 2006, F4D-1 (CD-ROM).
[3] N.Rueangsri and A.Thanachayanont, Coil design for optimum operating range of magnetically-coupled RFID system, Proc. of the International Symposium on Communications and Information Technologies 2006, 2006, F4D-2 (CD-ROM).
[4] J.H.Choi, D.Lee, Y.Youn, H.Jeon, and H.Lee, "Scanning-based pre-processing for enhanced RDIF Tag anti-collision protocols," Proc. of the International Symposium on Communications and Information Technologies 2006, 2006, F4D4 (CD-ROM).
[5] T.Tammet, J.Vain, and A.Kuusik, "Using RFID tags for robot swarm cooperation," WSEAS Transactions on Systems, Issue 5, Vol.5, 2006, pp.1121-1128.
[6] H.R.Choi, N.K.Park, B.J.Park, D.H.Yoo, H.K.Kwon, and J.J.Shin, "Design of RFID technology-based automated gate system in a container terminal," WSEAS Trans. on Systems, Issue 9, Vol.5, 2006, pp.2155-2163.
[7] M.S.Vlad and V.Sgarciu, "A RFID system designed for intelligent manufacturing process,"

WSEAS TRANSACTIONS on CIRCUITS AND SYSTEMS
[18] T.Tanzawa and T.Tanaka, A dynamic analysis of the Dickson charge pump circuit, T.IEEE, SolidState Circuits, Vol.32, No.8, 1997, pp.12371240.
[19] J.T.Wu and K.L.Chang, MOS charge pumps for low-voltage operation, T.IEEE, Solid-State Circuits, Vol.33, No.4, 1998, pp.592-597.
[20] T.Myono, A.Uemoto, S.Kawai, E.Nishibe, S.Kikuchi, T.Iijima, and H.Kobayashi, Highefficiency charge-pump circuits with large current output for mobile equipment applications, T.IEICE, Electron., Vol.E84-C, No.10, 2001, pp.1602-1611.
[21] H.San, H.Kobayashi, T.Myono, T. Iijima, and N. Kuroiwa, Highly-efficient low-voltageoperation charge pump circuits using bootstrapped gate transfer switches, T.IEEJ, Vol.120C, No.10, 2000, pp.1339-1345.
[22] K.Eguchi, H.Zhu, T.Tabata, F.Ueno, and T.Inoue, Design of a Dickson-type power converter with bootstrapped gate transfer switches, T. IEEJ, Vol.J124-C, No.7, 2004, pp.1416-1421.
[23] N.Hara, I.Oota, F.Ueno, and T.Inoue, A new ring type set-up switched-capacitor DC-DC converter with low inrush current at start-up and low current ripple in steady state, T. IEEJ, Vol.J81-CII, No.7, 1998, pp.600-612.
[24] N.Hara, I.Oota, I.Harada, and F.Ueno, Programmable ring type switched-capacitor DC-DC converters, T. IEEJ, Vol.J82-C-II, No.2, 1999, pp.56-68.
[25] K.Eguchi, F.Ueno, H.Zhu, T.Tabata, and T.Inoue, Design of a charge-average type SC DC-DC converter for cellular phone, T. IEEJ, Vol.125-C, No.1, 2005, pp.37-42.

## 7 Appendix

To save space, only the power efficiency of the conventional converter of Fig. 1 is analyzed, because the ripple voltage of the proposed converter and the conventional converter is almost the same as shown in Fig.9.

Firstly, the diode-switch is modeled by the circuit shown in Fig.11. In Fig.11, $V_{t h}$ is a voltage source to model the threshold voltage, $r_{f k}(k=1,2)$ denotes an on-resistance of the diode-switch, and $D_{i}$ denotes an ideal diode whose on-resistance is zero. Here, it is known that the diode current can be expressed by

$$
\begin{equation*}
I=I_{s}\left\{e^{q V /\left(k_{B} T_{a}\right)}-1\right\}, \tag{26}
\end{equation*}
$$



Fig. 11 Model of diode-switch.

(a)

(b)

Fig. 12 Instantaneous equivalent circuits of the conventional converter block. (a) State $-T 1$. State - T2.
where $I_{s}, T_{a}$, and $k_{B}$ denote a saturation current, an absolute temperature, and the Boltzmann's constant, respectively. From Eq.(26), $r_{f k}$ can be derived as follows:

$$
\begin{align*}
r_{f k} & =\left(\frac{d I}{d V}\right)^{-1}=\frac{k_{B} T_{a}}{q I_{s} e^{q V /\left(k_{B} T_{a}\right)}}, \\
& \simeq \frac{k_{B} T_{a}}{q I} . \tag{27}
\end{align*}
$$

From Figs. 1 and 11, the instantaneous equivalent circuits of the converter block are expressed by the circuits shown in Fig. 12.

For easy understanding of the circuit operation, let us consider the converter block-1. In the case of State $-T 1$, the differential values of the electric charges in the input and the output terminals, $\Delta q_{T 1, V_{\text {in }}}$ and $\Delta q_{T 1, V_{\text {out }}}$, are given by

$$
\text { and } \quad \begin{align*}
\Delta q_{T 1, V_{\text {in }}} & =\Delta q_{T 1}^{1}\left(1+\tan \delta_{1}\right) \\
\Delta q_{T 1, V_{\text {out }}} & =\Delta q_{T 1}^{2}\left(1+\tan \delta_{2}\right) \\
& -\Delta q_{T 1}^{1}\left(1+\tan \delta_{1}\right),
\end{align*}
$$

respectively. On the other hand, in the case of State $T 2, \Delta q_{T 2, V_{i n}}$ and $\Delta q_{T 2, V_{o u t}}$, are given by

$$
\begin{array}{ll} 
& \Delta q_{T 2, V_{\text {in }}}=\Delta q_{T 2}^{1}\left(1+\tan \delta_{1}\right) \\
\text { and } & \Delta q_{T 2, V_{\text {out }}}=\Delta q_{T 2}^{2}\left(1+\tan \delta_{2}\right),
\end{array}
$$

respectively. Since the electric charges in the input and the output, $\Delta q_{V_{\text {in }}}$ and $\Delta q_{V_{o u t}}$, can be expressed by Eq.(5), the following equations are derived by substituting Eqs.(28) and (29) into Eq.(5):

$$
\begin{align*}
\Delta q_{V_{\text {in }}} & =2 \Delta q_{T 1}^{1}\left(1+\tan \delta_{1}\right), \\
\Delta q_{V_{\text {out }}} & =-\Delta q_{T 1}^{1}\left(1+\tan \delta_{1}\right), \\
\overline{I_{\text {in }}} & =-2 \overline{I_{\text {out }}} . \tag{30}
\end{align*}
$$

In Fig.12, the energy consumed by resistors in 1period, $W_{S C}$, can be expressed by

$$
\begin{equation*}
W_{S C}=W_{T 1}+W_{T 2}, \tag{31}
\end{equation*}
$$

where

$$
\begin{aligned}
W_{T 1} & =\frac{\left(R_{i n}+r_{f 1}\right) \cdot\left\{\Delta q_{T 1}^{1}\left(1+\tan \delta_{1}\right)\right\}^{2}}{T 1} \\
& +\frac{R_{\delta 1} \cdot\left(\Delta q_{T 1}^{1} \tan \delta_{1}\right)^{2}}{T 1}+\frac{R_{\delta 2} \cdot\left(\Delta q_{T 1}^{2} \tan \delta_{2}\right)^{2}}{T 1}
\end{aligned}
$$

and

$$
\begin{align*}
W_{T 2}= & \frac{\left(R_{i n}+r_{f 2}\right) \cdot\left\{\Delta q_{T 2}^{1}\left(1+\tan \delta_{1}\right)\right\}^{2}}{T 2} \\
& +\frac{R_{\delta 2} \cdot\left(\Delta q_{T 2}^{2} \tan \delta_{2}\right)^{2}}{T 2} . \tag{3}
\end{align*}
$$

In Fig. 12 (a) and (b), the following equations can be obtained by Kirchhoff's law:

$$
\begin{aligned}
\left(\overline{V_{i n}}-V_{t h 1}\right) T 1 & =R_{\delta_{2}} \Delta q_{T 1}^{2} \tan \delta_{2} \\
& -R_{\delta_{1}} \Delta q_{T 1}^{1} \tan \delta_{1} \\
& -\left(R_{i n}+r_{f 1}\right)\left(1+\tan \delta_{1}\right) \Delta q_{T 1}^{1}
\end{aligned}
$$

and

$$
\begin{align*}
-\left(\overline{V_{i n}}-\right. & \left.V_{t h 2}\right) T 2=R_{\delta_{1}} \Delta q_{T 2}^{1} \tan \delta_{1} \\
& +\left(R_{\text {in }}+r_{f 2}\right)\left(1+\tan \delta_{1}\right) \Delta q_{T 2}^{1} . \tag{32}
\end{align*}
$$

Here, we define that $V_{t h} \equiv V_{t h 1}=V_{t h 2}$. By substituting Eqs.(2) and (10) into (32), the following equation is obtained:

$$
\begin{align*}
& \Delta q_{T 1}^{2} \tan \delta=-\frac{2 \Delta q_{V_{\text {out }}}}{R_{\delta}(1+\tan \delta)} \\
& \quad .\left\{R_{\text {in }}+r_{f}+\left(R_{\text {in }}+R_{\delta}+r_{f}\right) \tan \delta\right\}, \tag{33}
\end{align*}
$$

where

$$
r_{f} \equiv \frac{r_{f 1}+r_{f 2}}{2} .
$$

Therefore, we can derive the following equations by substituting Eq.(33) into Eq.(31):

$$
W_{T 1}=2\left(R_{\text {in }}+r_{f 1}\right) \frac{\left(\Delta q_{V_{\text {out }}}\right)^{2}}{T}
$$

$$
\begin{align*}
& W_{T 2}=2\left(R_{\text {in }}+r_{f 2}\right) \frac{\left(\Delta q_{V_{\text {out }}}\right)^{2}}{T} \\
& +2 R_{\delta}\left[\frac{2\left\{R_{\text {in }}+r_{f}+\left(R_{\text {in }}+R_{\delta}+r_{f}\right) \tan \delta\right\}}{R_{\delta}(1+\tan \delta)}\right]^{2} \\
& \quad \cdot \frac{\left(\Delta q_{V_{\text {out }}}\right)^{2}}{T} . \tag{34}
\end{align*}
$$

Since the consumed energy $W_{S C}$ in Fig. 6 is defined by Eq.(13), the resistance $R_{S C}$ of the conventional converter block is obtained by Eqs.(13) and (34) as follows:

$$
\begin{aligned}
& R_{S C}=4\left(R_{i n}+r_{f}\right)+2 R_{\delta}\left(\frac{\tan \delta}{1+\tan \delta}\right)^{2} \\
& \quad+16 R_{\delta}\left\{\frac{R_{i n}+r_{f}+\left(R_{i n}+R_{\delta}+r_{f}\right) \tan \delta}{R_{\delta}(1+\tan \delta)}\right\}^{2} .
\end{aligned}
$$

Hence, from Eqs.(30) and (35), the equivalent circuit of the proposed converter can also be expressed by the circuit shown in Fig.7. The difference between the proposed converter and the conventional converter is $R_{S C}$.

From Eqs.(14), (18), and (35), the power efficiency of the conventional converter and the proposed converter is the same if $R_{o n}=r_{f}$. As Eq.(27) shows, however, $r_{f}$ is in inverse proportion to the diode current $I$. In other word, $r_{f}$ becomes large when the output load $R_{L}$ is large, because $I$ decreases in proportion to $R_{L}$. Therefore, in the conventional converter, the power efficiency $\eta$ decreases greatly at high $R_{L}$. This result agrees well with the simulation result of Fig.9.


[^0]:    ${ }^{1}$ In Fig.1, $D$ denotes a duty factor.
    ${ }^{2}$ The conventional converter of Fig. 1 consists of 4 diodeswitches and 3 capacitors. On the other hand, the proposed converter of Fig. 3 can be constructed with 4 MOS switches and 3

[^1]:    ${ }^{4}$ The comparison of the power efficiency between the proposed converter and the conventional converter will be discussed in Appendix.

[^2]:    ${ }^{5}$ In the experiment, the circuit properties such as power efficiency, ripple noise, etc. were not examined, because the experimental circuit was built with commercially available transistors on the bread board. Only the circuit design was verified through this experiment. The IC implementation and experiments are left to the future study.

